

# Solution Processing of Semiconducting Organic Molecules for Tailored Charge Transport Properties

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We studied the charge transport characteristics of the organic semiconductor 6,13-bis(tri isopropyl silyl ethynyl) pentacene (TIPS-PEN) deposited by dip-coating of a solution in an azeotropic solvent mixture. Arrays of crystalline ribbons were obtained with a morphology controllable by variation of the coating speed  $U$ . The charge carrier mobility  $\mu$  exhibited a systematic and reproducible dependence on the coating speed  $U$  and maximum values as high as  $\mu \approx 1.0 \text{ cm}^2/(\text{V s})$ . [1]

We used isopropanol (IPA) and toluene, which exhibit a positive azeotropic point at a volume fraction (VF) of approximately 1/1. We typically use IPA/toluene VFs above 55/45, such that the vapor concentration of toluene exceeded its concentration in the liquid phase, which tends to enrich in IPA over time. The TIPS-PEN concentration was 1.5 wt%. In Fig. 2 we show the dependence of the average ribbon width  $\langle w \rangle$  and the fill factor  $f$  that were extracted from the optical microscopy images.

The ribbon width monotonically decreases with increasing dip-coating speed. The solid line corresponds to a power-law relation  $\langle w \rangle = b(U/U_0)^\alpha$  with  $U_0 = 0.12 \text{ mm/s}$  and fit parameters  $b = 5.5 \text{ }\mu\text{m}$  and  $\alpha = 0.94$ . Figure 3 presents the dependence of the field effect mobility  $\mu$  on the dip-coating speed. A very well-defined maximum of the carrier mobility  $\mu_{\text{max}} \approx 0.75 \text{ cm}^2/(\text{V s})$  is observed in the vicinity of  $U_{\text{opt}} = 0.02 \text{ mm/s}$ .

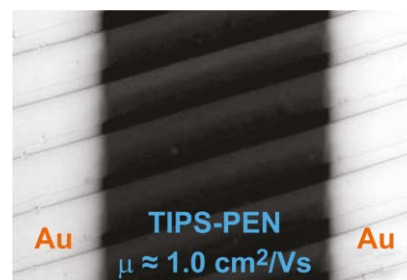


Fig. 1: Optical micrograph of TIPS-PEN crystal ribbons deposited on a Si substrate by means of solution crystallization. The white regions have increased reflectivity due to evaporated Au layers that form the source and drain contacts. Image width  $200 \text{ }\mu\text{m}$ .

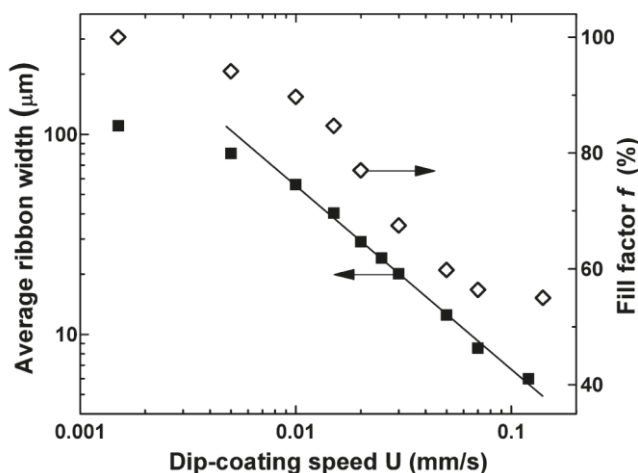


Fig. 2: Average TIPS-PEN ribbon width  $\langle w \rangle$  and fill factor  $f$  as a function of  $U$ .

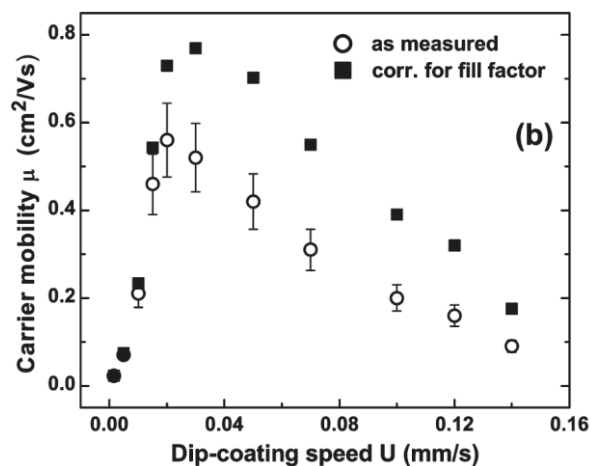


Fig. 3: Saturated carrier mobility  $\mu$  vs  $U$ .

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## References

1. R. Z. Rogowski, A. Dzwilewski, M. Kemerink, and A. A. Darhuber, *J. Phys. Chem. C* **115**, 11758–11762 (2011).
2. R. Z. Rogowski and A. A. Darhuber, *Langmuir* **26**, 11485–11493 (2010).